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Electronic Structure Study of CaCu₃Ti₄O₁₂ by means of X-ray Raman Scattering

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1 <u>Introduction</u>

A-site ordered perovskite CaCu₃Ti₄O₁₂ (CCTO) has attracted much attention recently, because it shows a giant dielectric constant ($\sim 10^5$) over a wide temperature range from about 100 to 600K and the dielectric constant decreases to one-hundredth without structural phase transition at the temperature under about 100K [1]. To clarify the nature of the anomalous dielectrics, electronic structure of CCTO should be investigated. Since X-ray Raman scattering (XRS) uses photons in both excitation and detection, it is effective in the study of electronic state of an insulator material. The results of XRS on Ti K edge of several Ti-oxides have been reported and showed scattering by Ti 2p3d and 2p4d core-excitations where underlines denote a core-hole [2]. The results on Cu K edge were also reported on CCTO [3]. In this study, XRS spectra of CCTO on both Ti K and Cu K edge were observed at low temperature and room temperature (RT).

2 Experiment

The polycrystalline sample of CCTO was used in this study. The XRS spectra were observed using X-ray emission spectrometer (ESCARGOT) at beamline BL-7C. Scattered photons were analyzed using crystals Ge(400) and Ge(444) in the measurements on Ti K and Cu K edge, respectively. A one-dimensional multi-channel proportional counter was used to detect the dispersed photons. The energy resolution of XRS measurement was about 1 eV.

3 Results and Discussion

Figure 1 is a comparison between the Ti K resonant XRS spectra of CCTO observed at RT and 20K. The XRS spectra are plotted against energy-loss from excitation (Raman shift). These spectra were excited at an energy just below the Ti 3d structure of Ti K absorption edge. We have reported that the P1~P4 are caused by the excitation of Ti $2\underline{p}3d$, while the P5~P7 are caused by the excitation of Ti $2\underline{p}4p$ [2]. The 3d peaks are split by ligand-field and spin-orbit interaction as shown in the figure. The figure shows the whole 3d structure becomes weak at 20K, while the 4p structure does not change. Since the XRS spectra reflect the density-of-state of unoccupied Ti 3d state, this result suggests the electron numbers in Ti 3d state increase at low temperature.

Figure 2 is a comparison between the Cu K resonant XRS spectra of CCTO observed at RT and 30K. The figure shows the peaks at about 930 and 950 eV (*) become weak at 30K. Since these peaks are specific peak



Fig. 1: Ti K resonant XRS spectra of CCTO observed at RT (dot) and 20K (line).



Fig. 2: Cu *K* resonant XRS spectra of CCTO observed at RT (dot) and 30K (line).

in XRS of the divalent Cu-compounds [4], these peaks should reflect the unoccupied Cu 3d state. This result suggests the electron numbers in Cu 3d state increase at low temperature.

In this study, increase of electron numbers at low temperature was observed in both Ti 3d and Cu 3d state. Though the results in this study cannot be connected to dielectric constant directly, XRS measurement would have possibility to clarify the origin of the anomalous dielectric constant.

References

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